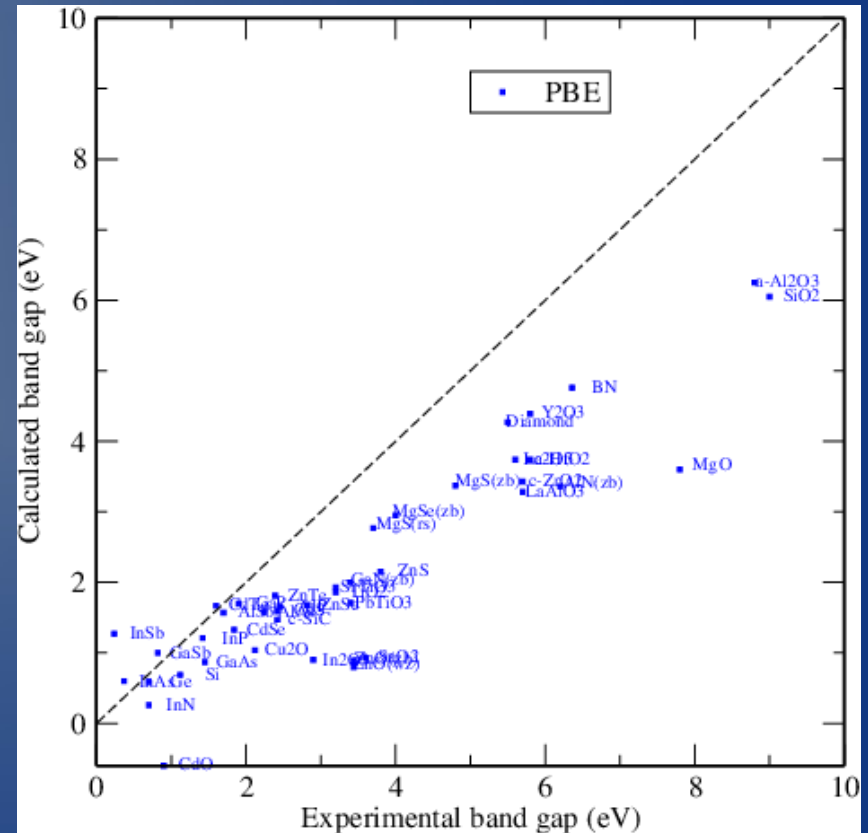


# Electronic band structure, sX-LDA, Hybrid DFT, LDA+U and all that

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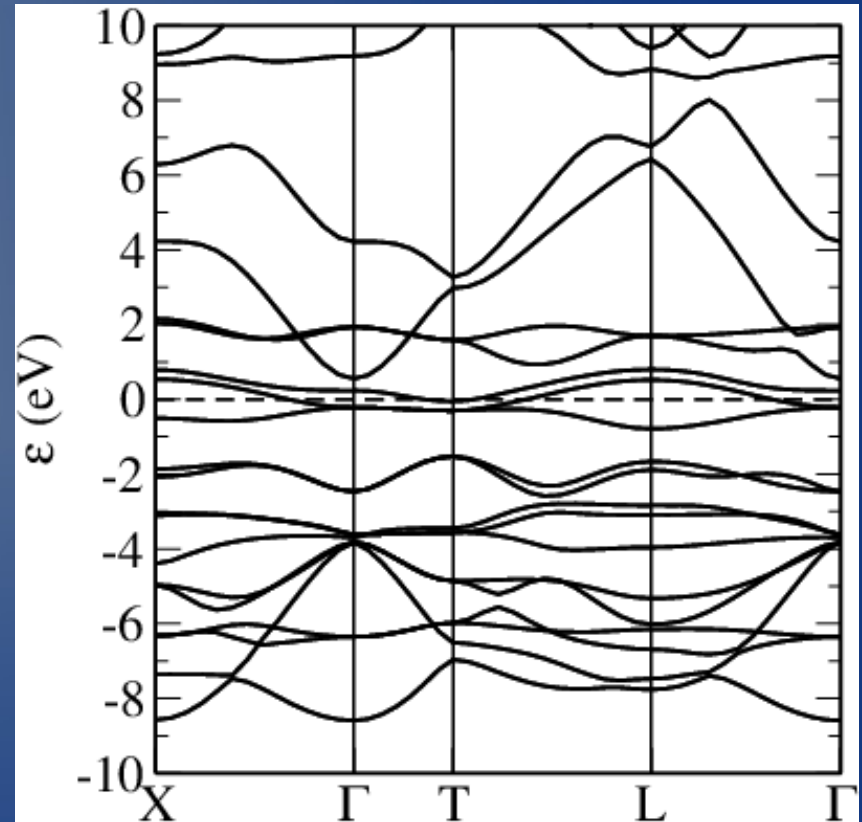
# LDA/GGA DFT is good but ...

- Naive LDA/GGA calculation severely underestimates band-gaps.
- Almost universal effect in wide-gap insulators and semiconductors.

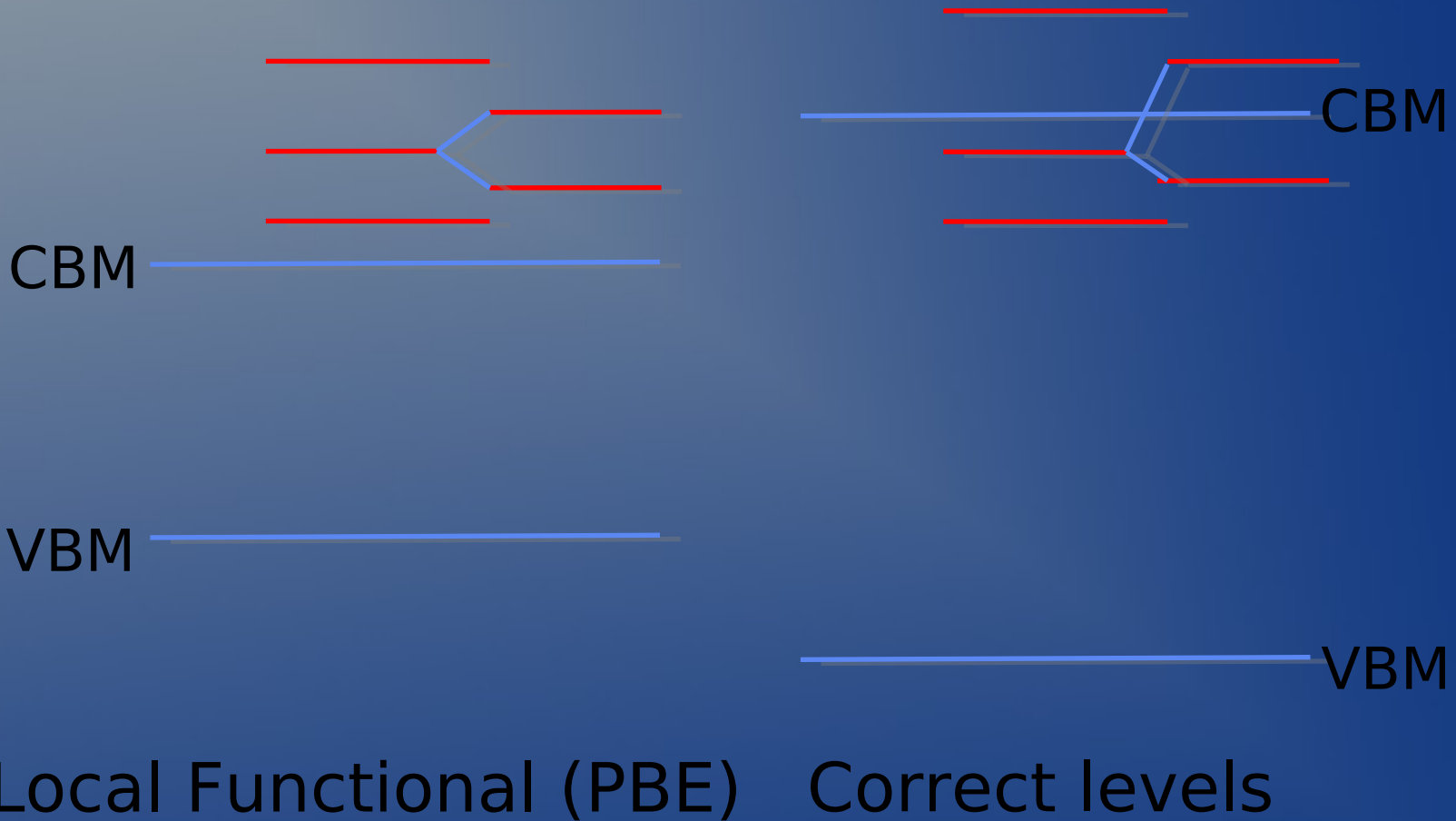


# Transition-metal Oxides

- TMOs are usually insulators
- FeO and many others predicted to be metallic in LDA/GGA
- Many so-called “strongly-correlated” oxides falsely predicted to be metallic



# Energy Levels of Defects



# Origin of band-gap problem

- DFT is only a ground state theory?

But band gap is a ground state property

$$E_{gap} = I - A = \{ E(N-1) - E(N) \} - \{ E(N) - E(N+1) \}$$

- Kohn-Sham states are not physical excitations – introduced to approximate K.E. by that K.E. of non-interacting system?
- XC potential  $V_{XC}$  has a fundamental discontinuity as function of occupancy not reproduced by LDA/GGA.

# The Fundamental Gap

- The fundamental gap is the IP – EA

- $E_{gap}^N = I - A = \{E(N-1) - E(N)\} - \{E(N) - E(N+1)\}$

- Or alternatively

- $E_{gap}^d = \left[ \frac{\partial E}{\partial N} \right]_{N+\delta} - \left[ \frac{\partial E}{\partial N} \right]_{N-\delta}$

- In the exact case these are equal.

- Therefore E(N) is composed of **straight line segments**

- For LDA/GGA  $E_{gap} = \epsilon_{KS}^{gap} = \epsilon_{HOMO}^{KS} - \epsilon_{LUMO}^{KS}$

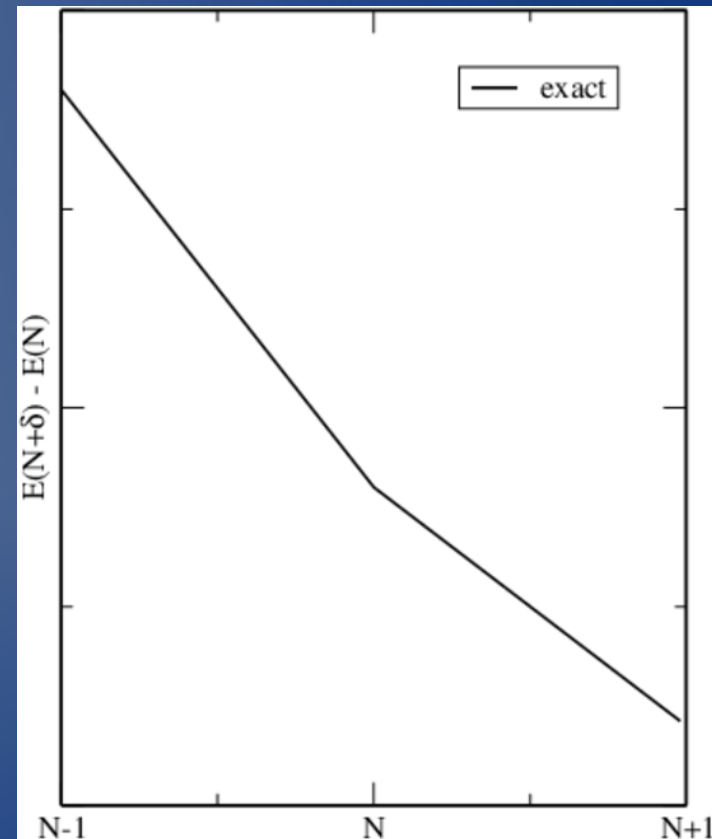
- Therefore for LDA/GGA  $\Delta_{XC} = 0$

- If Exc has orbital dependence

- $E_{gap}^N = \epsilon_{KS}^{gap} + \left[ \frac{\partial E}{\partial N} \right]_{N+\delta} - \left[ \frac{\partial E}{\partial N} \right]_{N-\delta}$

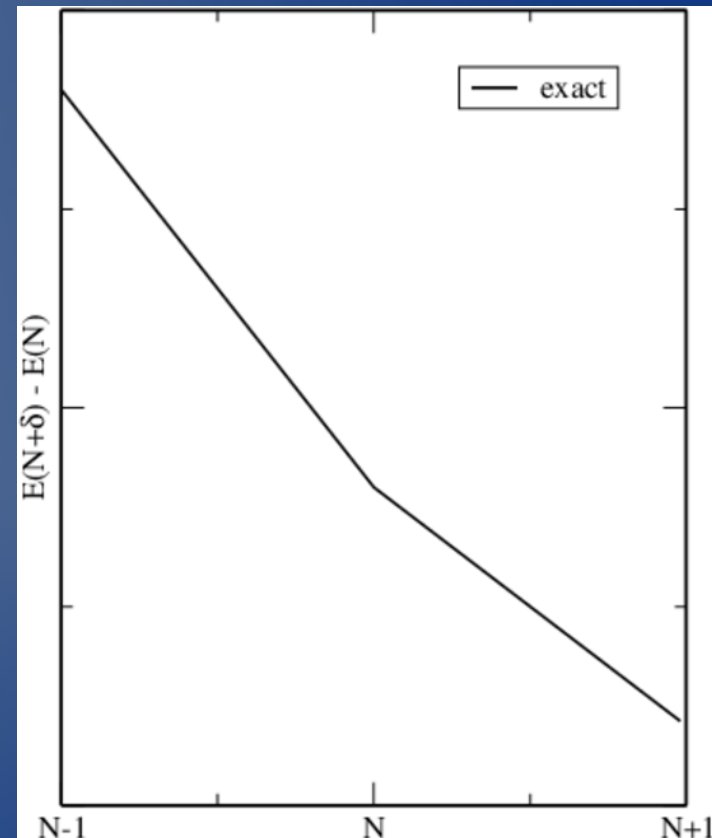
# Derivative Discontinuity

- Bandgap error related to energy/fractional occupancy curve (Perdew PRL 49, 1691 (1982))



# Derivative Discontinuity

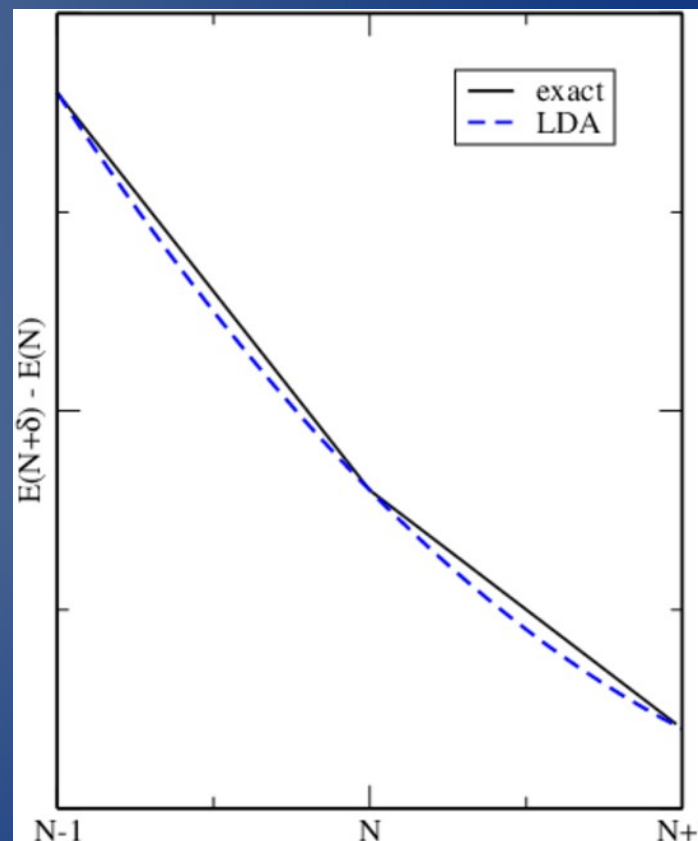
- Bandgap error related to energy/fractional occupancy curve (Perdew PRL 49, 1691 (1982))
- exact energy/occupancy curve **linear** with +ve derivative discontinuity  $\Delta_{XC} > 0$





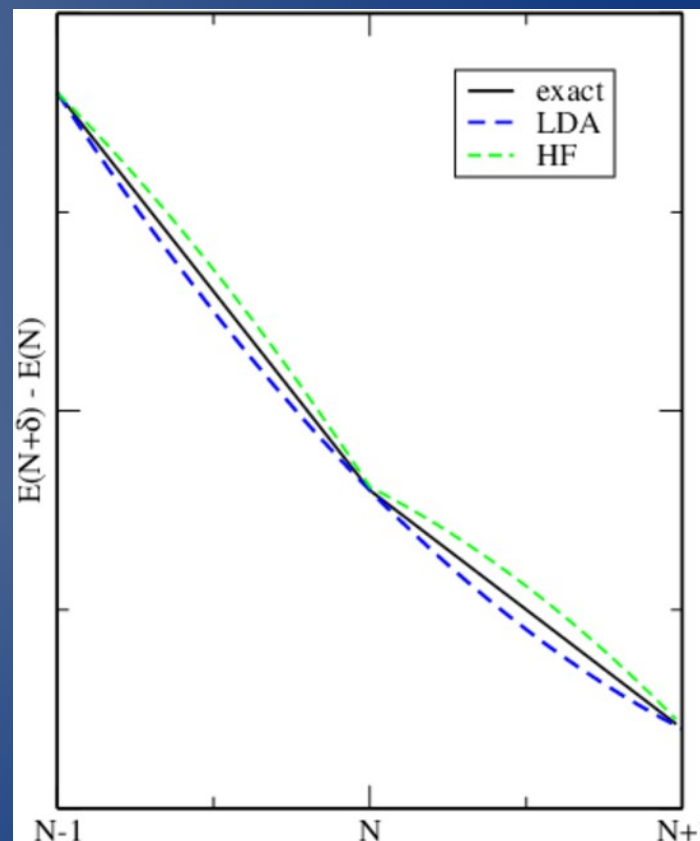
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- Bandgap error related to energy/fractional occupancy curve (Perdew PRL 49, 1691 (1982))
- exact energy/occupancy curve **linear** with +ve derivative discontinuity  $\Delta_{XC} > 0$
- LDA/GGA form is convex with zero derivative discontinuity.  $\Delta_{XC} = 0$
- HF form is concave with -ve derivative discontinuity.  $\Delta_{XC} < 0$



# Self-interaction error

- Consider Hartree (Coulomb) energy term in Hamiltonian

$$E_H = \frac{1}{2} \iint d^3r d^3r' \frac{n(\mathbf{r})n(\mathbf{r}')}{|\mathbf{r}-\mathbf{r}'|} = \frac{1}{2} \sum_{i,j} \iint d^3r d^3r' \frac{\psi_i^*(\mathbf{r})\psi_i(\mathbf{r})\psi_j^*(\mathbf{r}')\psi_j(\mathbf{r}')}{|\mathbf{r}-\mathbf{r}'|}$$

- Includes self-interaction contribution

$$E_H^{\text{self}} = \frac{1}{2} \sum_i \iint d^3r d^3r' \frac{\psi_i^*(\mathbf{r})\psi_i(\mathbf{r})\psi_i^*(\mathbf{r}')\psi_i(\mathbf{r}')}{|\mathbf{r}-\mathbf{r}'|}$$

- Exactly cancelled by  $i=j$  terms of Hartree Fock exchange

$$E_X = -\frac{1}{2} \sum_{i,j} \iint d^3r d^3r' \frac{\psi_i^*(\mathbf{r})\psi_j(\mathbf{r})\psi_i^*(\mathbf{r}')\psi_j(\mathbf{r}')}{|\mathbf{r}-\mathbf{r}'|}$$

- But only 93% cancelled by LDA exchange (in H atom)
- LDA electron “sees” extra Coulomb repulsion by own charge  
=> can reduce energy by unphysical delocalisation.
- d-bands in TMs too wide, and too high in energy, closing gap

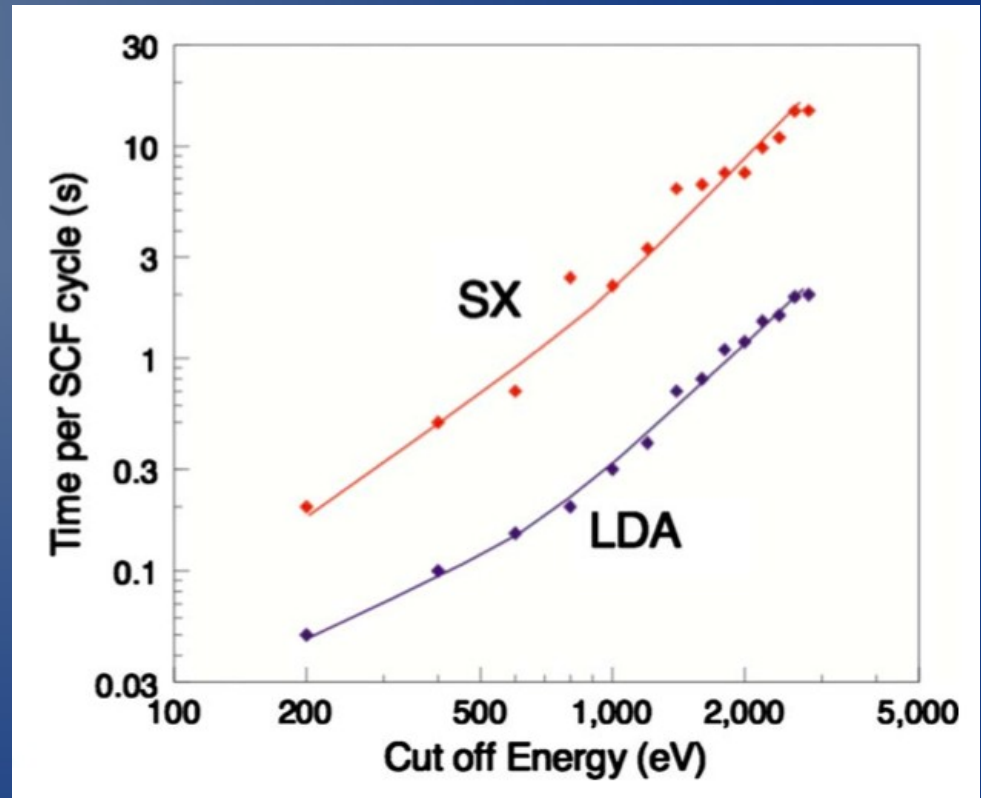
# Non-local functionals

- Now well-known and commonly used zoo of non-local functionals (HSE, PBE0, B3LYP)
- Mix a fraction of non-local HF with local correlation
- Advantages:
  - They correct (more or less!) the band gap underestimate
  - They are energy functionals in the DFT sense
  - Can be used in the favoured energy minimisation techniques for SCF solution
  - Can calculate forces (important!)
  - Appear to correct the localisation error
- Disadvantages
  - Computationally expensive
  - Still investigating how well they perform (still rather empirical)

# Computational Expense

$$-\frac{1}{2}\nabla^2\psi_i(\mathbf{r})+V_{loc}(\mathbf{r})\psi_i(\mathbf{r})+\int V_{XC}^{NL}(\mathbf{r},\mathbf{r}')\psi_i(\mathbf{r}')d^3\mathbf{r}'=\epsilon_i\psi_i(\mathbf{r})$$

- Require solutions of the **non-local** Schrödinger equation
- VNL incorporates HF-like terms
- Extra integral over  $r'$  multiplies computational cost with a plane-wave basis set
- Actually solve in recip space using FFT convolution.



Overall scaling  $T \propto N_{PW} \times N_k^2 \times N_b^2$

# Hybrid Functionals

PBEh (PBE0): simple mixture of exact exchange

$$E_{xc}^{PBEh} = \alpha E_x^{HF} + (1-\alpha) E_x^{PBE} + E_c^{PBE}; \alpha = 1/4$$

B3LYP: more complex mixture of exact exchange

HSE: range-separated version

$$\frac{1}{r} = \text{SR} + \text{LR} = \frac{\text{erfc}(\omega r)}{r} + \frac{\text{erf}(\omega r)}{r}$$

$$E_{xc}^{\omega PBEh} = \alpha E_x^{HF,SR}(\omega) + (1-\alpha) E_x^{PBE,SR}(\omega) + E_{LR}^{PBE}(\omega) + E_c^{PBE}$$

# Screened Exchange

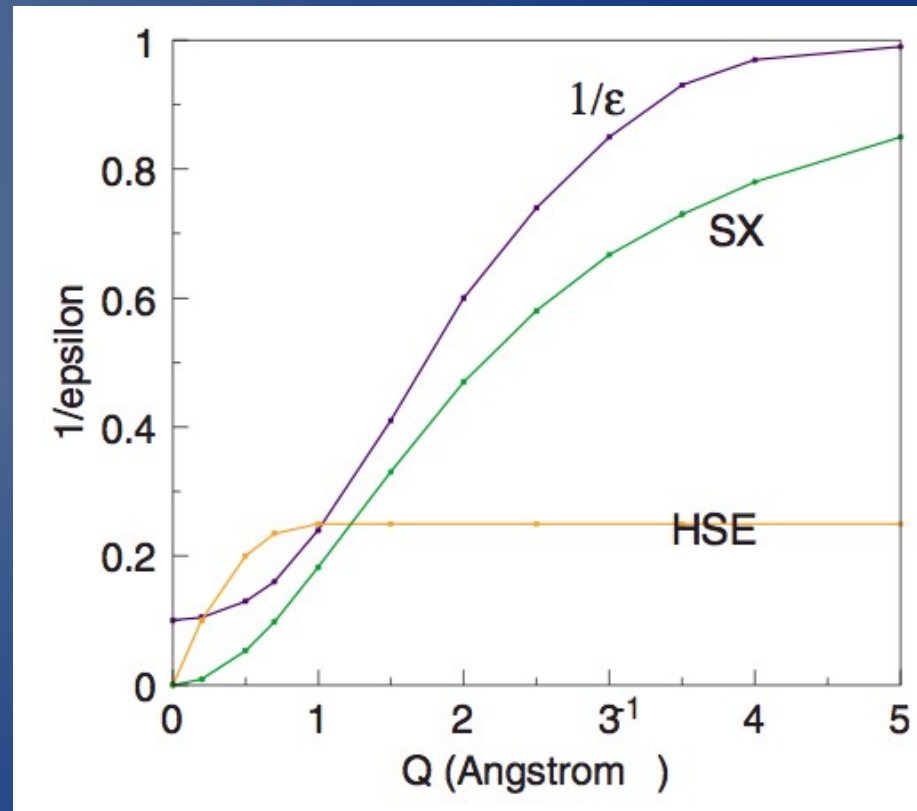
- The sX potential is non-local
- Replaces the LDA with short-ranged Thomas-Fermi screened Coulombic exchange potential

$$V_j^{sX}(\mathbf{r}, \mathbf{r}') = - \sum_i \frac{\psi_i(\mathbf{r}) \exp[-(k_s |\mathbf{r} - \mathbf{r}'|)] \psi_j^*(\mathbf{r}')}{|\mathbf{r} - \mathbf{r}'|} + \epsilon_{loc}^{LDA}(n) - \int V_X^{LDA}(n) F(n) n(\mathbf{r}) d\mathbf{r}$$

- Here  $k_s$  is the Thomas-Fermi screening length where the density of valence (non-d) electrons is screened
- See Clark and Robertson, PRB 82 085208 (2010) for details

# Screening

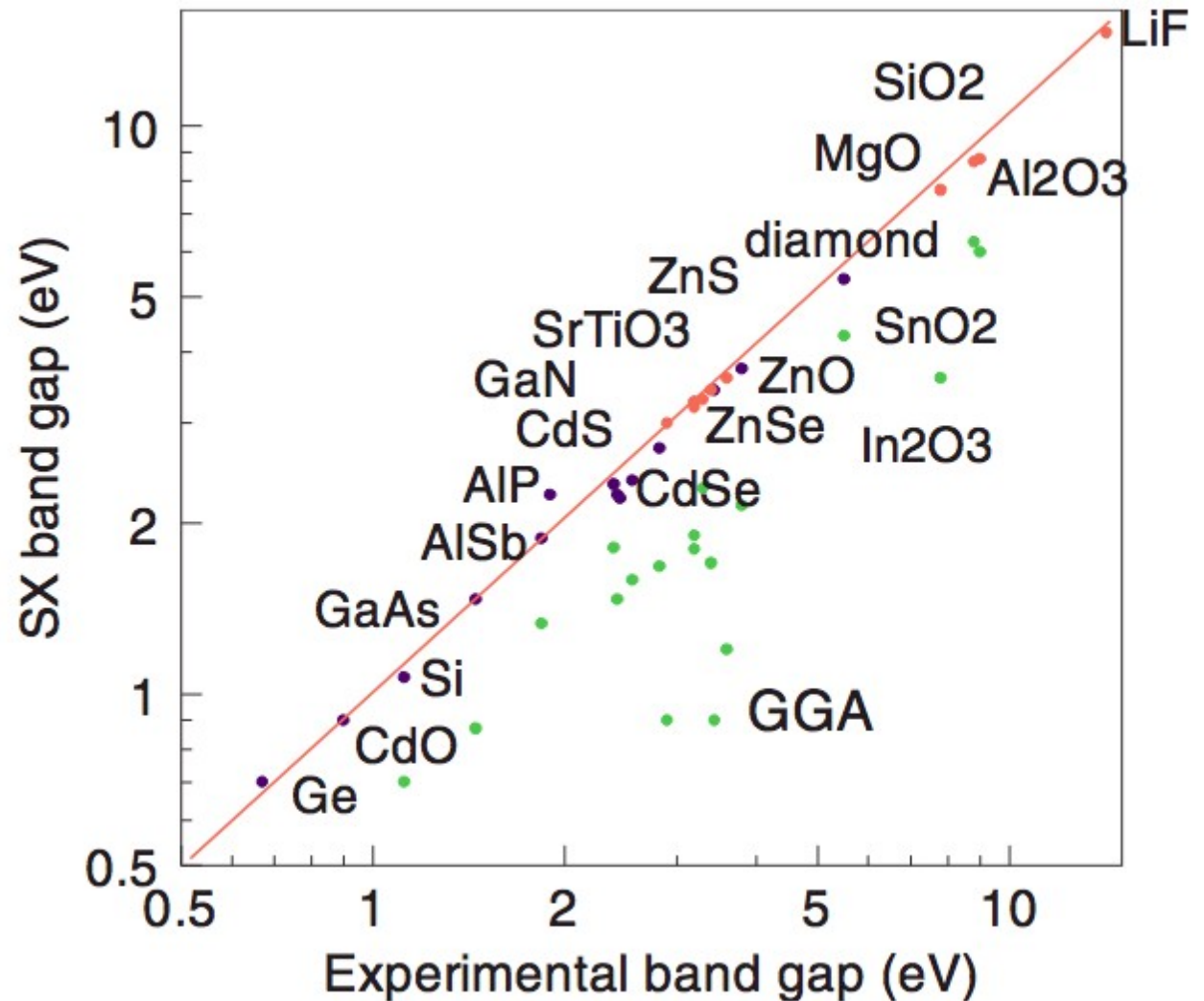
- Comparison of screening in HSE and sX
- sX has the correct asymptotic limits in the free-electron gas
- Note that the screening is similar to the inverse dielectric function (in this case GaAs)
- This is expected with TF screening (zeroth order approximation to semiconductor's screening)





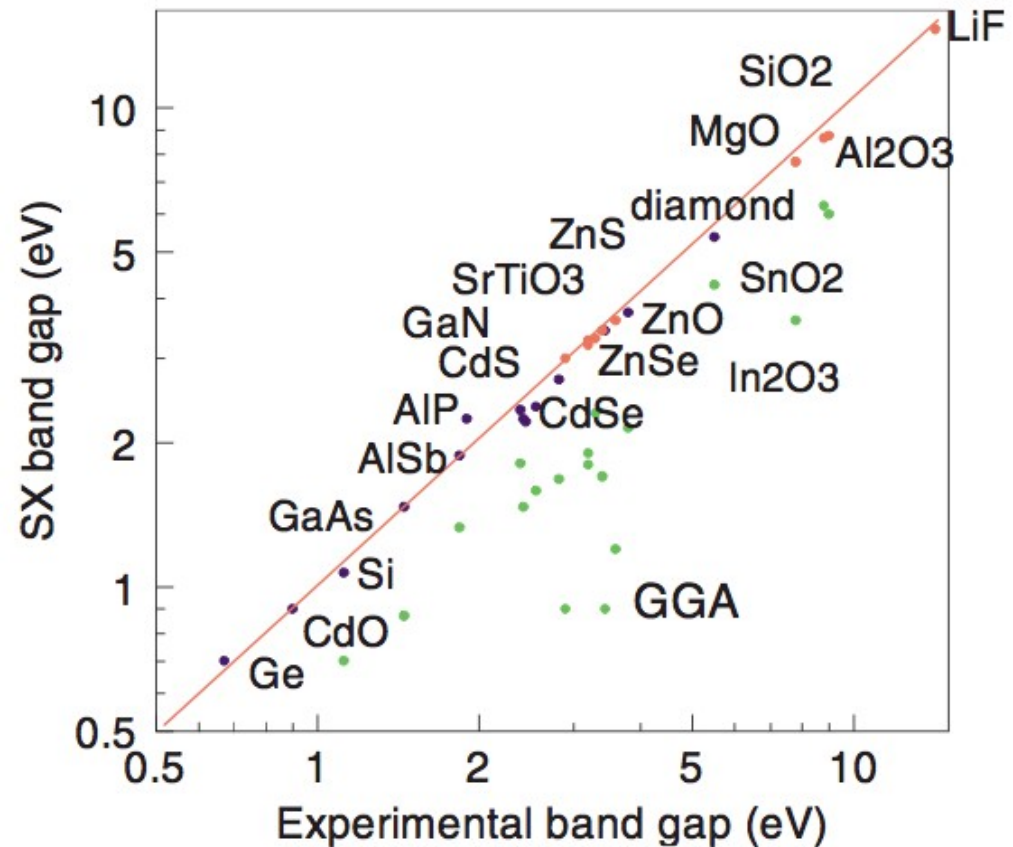
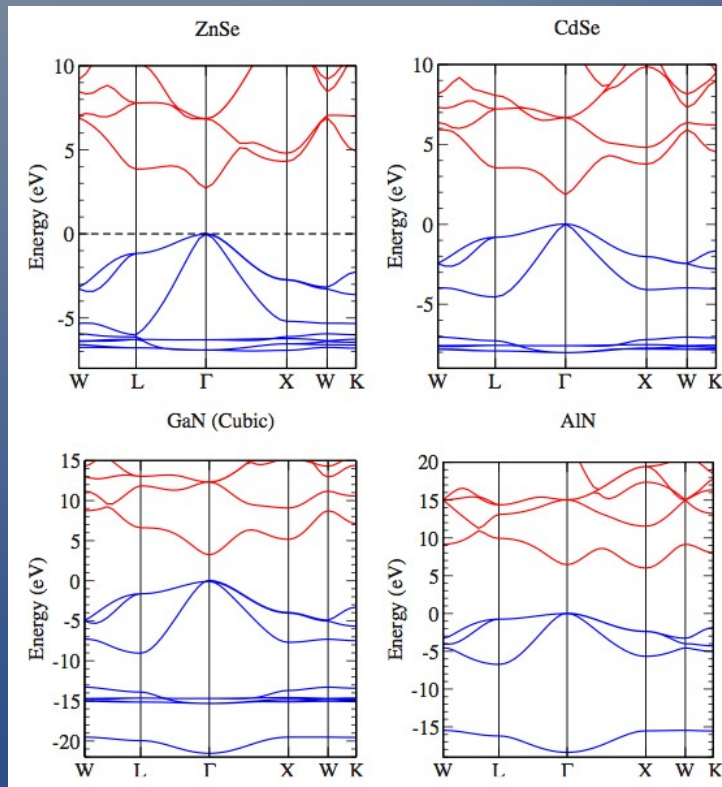
# sX Band Gaps

- Closely related HSE (HSE06) gaps are fairly similar
- Functional forms are different but both have a short-ranged screening of the HF component

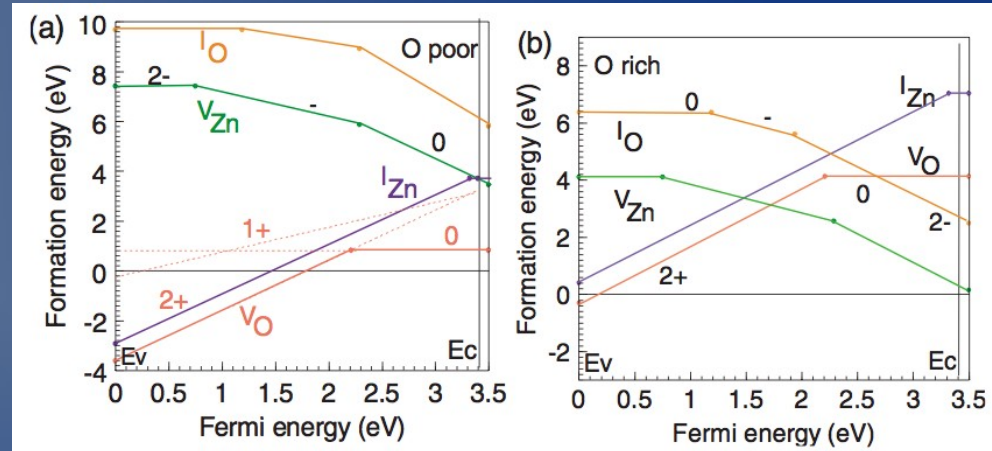
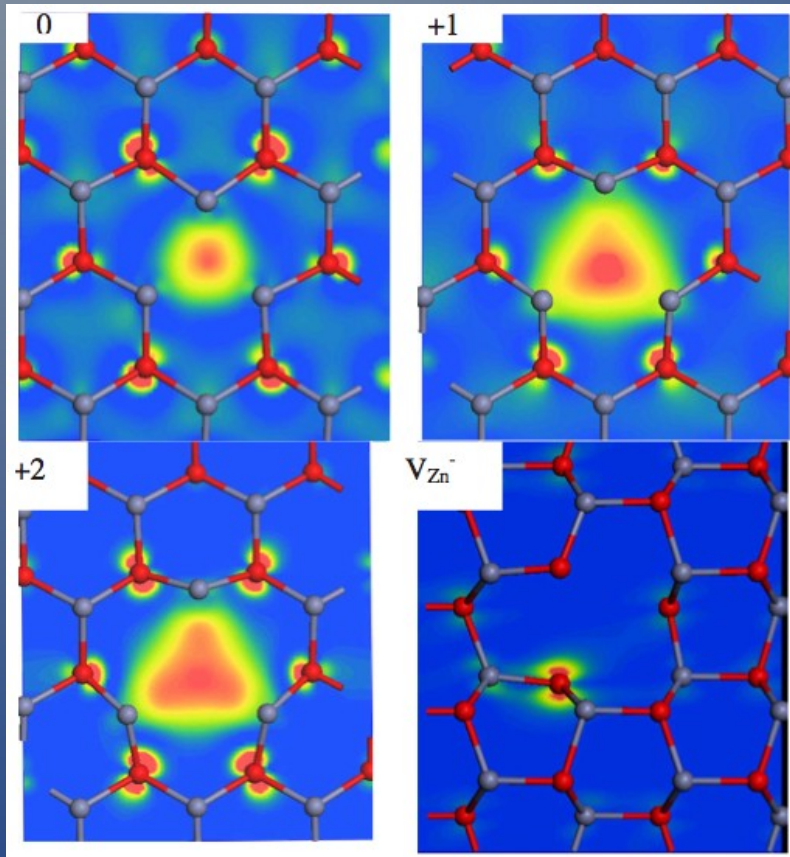


# SX bandgaps

DFT and excitation energies are now a reality!



# ZnO Defects



- Accurate prediction of:
  - Geometry of defects
  - Band Gap
  - Formation Energies

Clark, Zunger, et al., PRB 81, 115311 (2010)

# CASTEP implementation

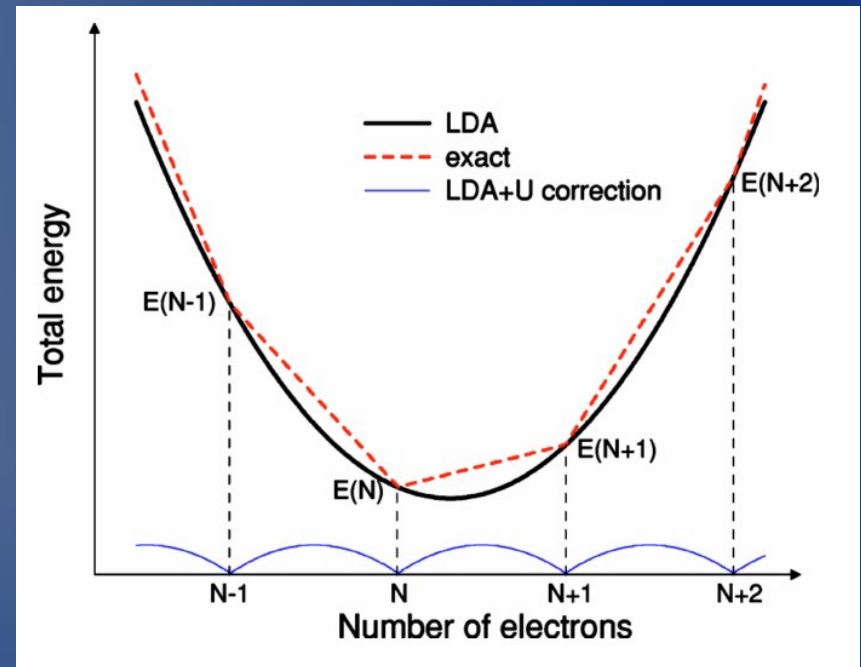
- CASTEP has implemented sX-LDA, PBE0, B3LYP
- Currently restricted to norm-conserving pseudopotentials.
- Only LDA or GGA pseudopotentials are available or can be generated.
- Density mixing scheme does not work: use `FIX_OCCUPANCY` mode, and `allbands/EDFT` SCF solver.
- To accelerate k-point convergence turn on divergence correction (Gygi and Baldereschi, PRB 34, 4405 (1986))
- Still very expensive compared to LDA/GGA

# Adding an on-site Hubbard U

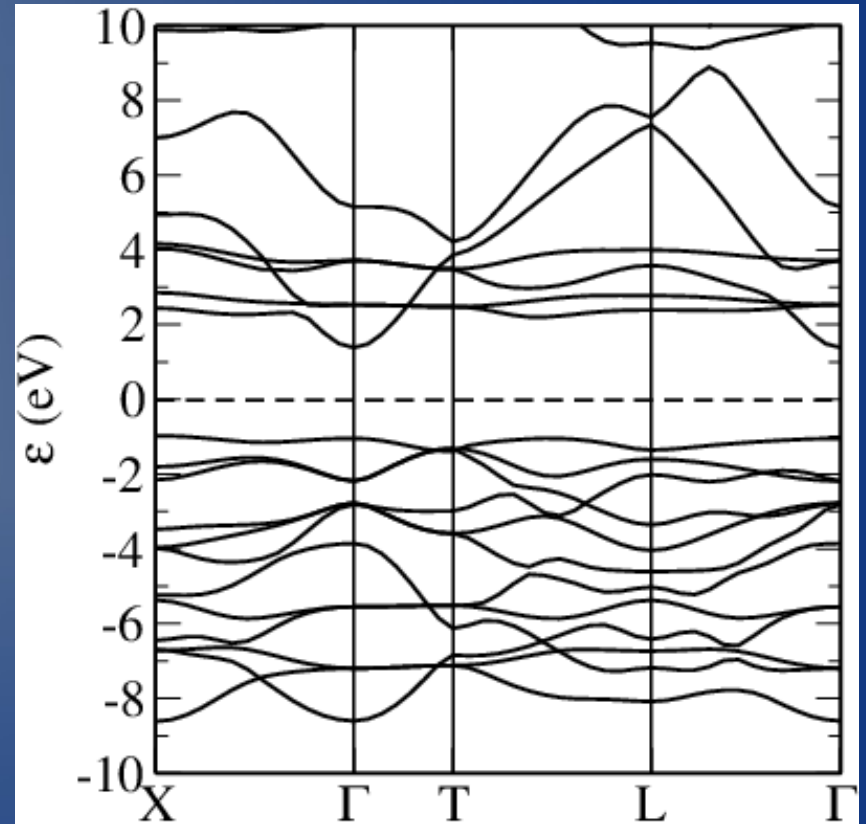
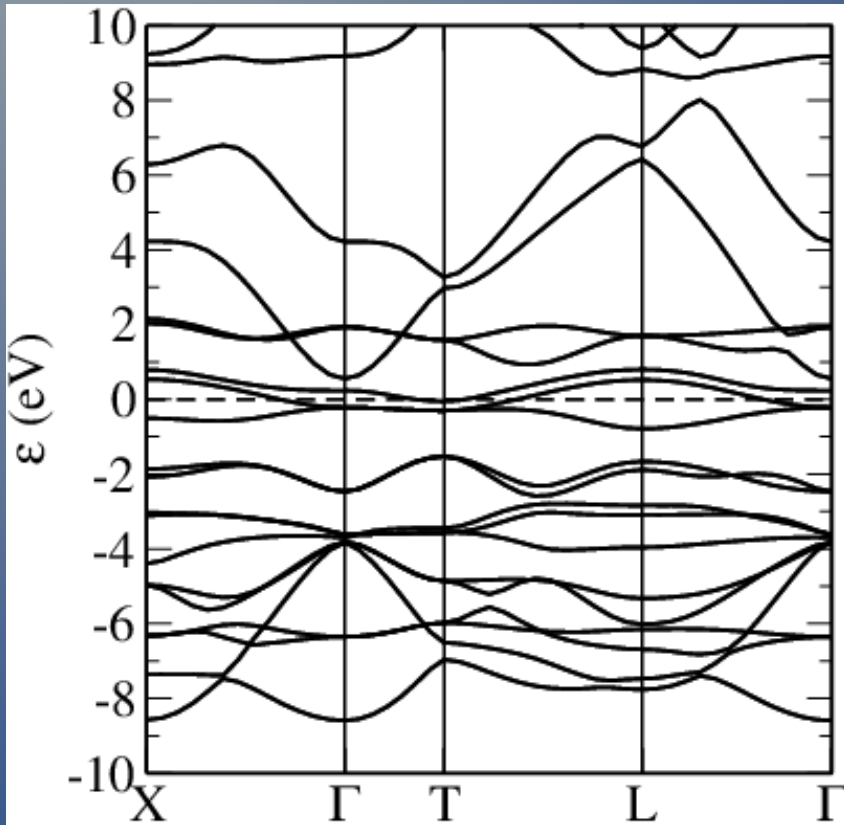
- Hubbard model favours integer occupancies
- Add term to Hamiltonian modelling on-site repulsion scaled by “U”

$$E_U = \frac{U}{2} \sum_{l,\sigma} \text{Tr}[n^{l,\sigma}(1-n^{l,\sigma})]$$

- U may be derived for bulk system by linear response
- No nonlocal integrals required - much cheaper than exact exchange.



# Effect of U on FeO



- GGA+U opens gap between unoccupied and occupied d-states in open-shell systems
- Does not give good band gaps for closed-shell systems.

# Hybrid, sX, LDA+U merits and demerits

- Hybrid functionals can correct band-gaps, but do fail to reproduce correct screening. Poor performance for metallic systems. Reasonable for TMOs. Very expensive.
- SX-LDA with TF screening length good for bulk, closed-shell systems. Screening model good for large Q. But what screening length to use for structured model systems? Expensive.
- LDA+U correctly splits partially occupied d- and f-shells in magnetic system. Some correction of self-interaction error, but worse bandgaps than sX and hybrids. Poor bandgaps for closed-shell systems with sane U.
- ALL these are MODEL methods (not ab initio) and all involve some parameterization.